

# PRM021N06N5

# PFC Device Corporation

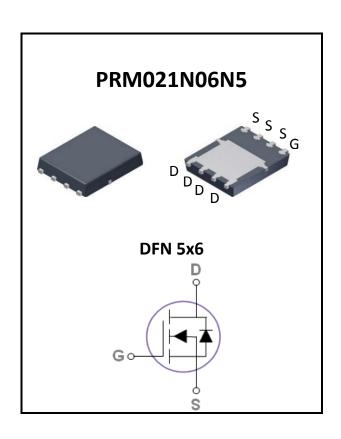
# 60V Single N-Channel MOSFET

### Major ratings and characteristics

Characteristics	Values	Units
$V_{DS}$	60	٧
I <sub>D</sub> (T <sub>C</sub> =25°C)	30	Α
Max. R <sub>DS(ON)</sub>	21	mΩ
T <sub>J</sub> Operating Junction Temperature	-55 to +150	°C

## **General Description**

The N-Channel enhancement mode power field effect transistor is using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. The device is well suited for high efficiency fast switching applications.



# **Typical Applications**

- Charger Adapter
- Power Tools
- LED Lighting

#### **Features**

- Max.  $R_{DS(ON)}=21m\Omega@V_{GS}=10V$
- Improved dv/dt capability
- Fast switching
- 100% E<sub>AS</sub> Guaranteed
- Green Device Available

# 1. Characteristics

**Maximum Ratings Characteristics** 

( $T_A = 25$  °C unless otherwise specified)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	±20	V
1	Drain Current – Continuous (T <sub>C</sub> =25°C)	30	Α
I <sub>D</sub>	Drain Current – Continuous (T <sub>C</sub> =100°C)	19	Α
I <sub>DM</sub>	Drain Current – Pulsed <sup>1</sup>	80	Α
$E_AS$	Single Pulse Avalanche Energy <sup>2</sup>	12	mJ
$I_{AS}$	Single Pulse Avalanche Current <sup>2</sup>	16	Α
D	Power Dissipation (T <sub>C</sub> =25°C)	37	W
$P_D$	Power Dissipation – Derate above 25°C	0.3	W/°C
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C

#### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient		62	°C/W
$R_{ heta JC}$	Thermal Resistance Junction to Case		3.3	°C/W



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#### **Electrical Characteristics**

(T<sub>J</sub> = 25 °C unless otherwise specified)

#### **Off Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60			V
1	Duein Course Looke as Course	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C			1	uA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C			250	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±100	nA

#### On Characteristics

R <sub>DS(ON)</sub> Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =15A		17	21	mΩ	
$R_{DS(ON)}$		V <sub>GS</sub> =4.5V, I <sub>D</sub> =8A		20	24	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.0	1.8	3.0	<b>V</b>
$g_{fs}$	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =20A	1	50		S

**Dynamic and switching Characteristics** 

Dynamic and contenting characteriones						
$Q_{q}$	Total Gate Charge			20		
$Q_{qs}$	Gate-Source Charge	$V_{DS}$ =30V, $V_{GS}$ =10V, $I_{D}$ =20A		4.6		nC
$Q_{gd}$	Gate-Drain Charge			3.2		
$T_{d(on)}$	Turn-On Delay Time			11		
T <sub>r</sub>	Turn-On Rise Time	$V_{DD}$ =30V, $V_{GS}$ =10V, $R_{G}$ =6 $\Omega$		80		20
$T_{d(off)}$	Turn-Off Delay Time		1	25		ns
$T_f$	Turn-Off Fall Time		-	86		
C <sub>iss</sub>	Input Capacitance		1	1200		
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz	ł	100		pF
$C_{rss}$	Reverse Transfer Capacitance		1	65		
$R_{g}$	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		2.8		Ω

#### **Drain-Source Diode Characteristics**

$V_{SD}^{3}$	Source to Drain Diode Voltage	$V_{GS}$ =0V, $I_{S}$ =20A	 	1.5	V
t <sub>rr</sub>	Reverse Recovery Time	1 -20	 5		ns
$Q_{rr}$	Reverse Recovery Charge	I <sub>S</sub> =20A, di/dt=100A/us	 0.5		nC

#### Note:

- 1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
- 2.  $V_{DD}$ =50V,  $V_{GS}$ =10V, L=0.1mH,  $I_{AS}$ =16A,  $R_{G}$ =25 $\Omega$ , Starting TJ=25 $^{\circ}$ C
- 3. The data tested by pulsed, pulse width  $\leq$ 300us, duty cycle  $\leq$ 2%.

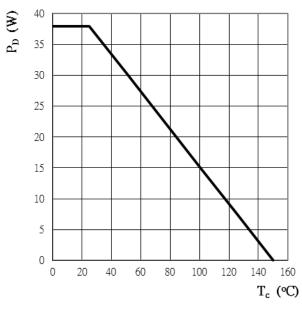


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# 2. Characteristics Curves

## **Ratings and Characteristics Curves**

## ( T<sub>A</sub> = 25° unless otherwise specified )



35 30 25 20 15 10 5 0 25 50 75 100 125 150 T<sub>c</sub> (°C)

Figure 1: Power Dissipation

Figure 2: Continuous Drain Current vs. T<sub>C</sub>

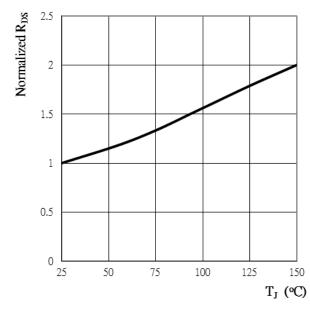


Figure 3: Normalized RDSON vs. T<sub>J</sub>

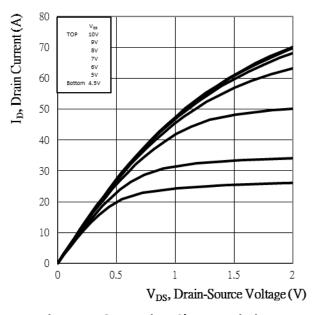
Figure 4: Normalized BVDSS vs. T<sub>J</sub>



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#### **Ratings and Characteristics Curves**

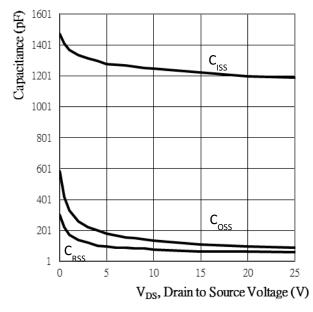
## ( T<sub>A</sub> = 25° unless otherwise specified )



RDS(ON) (m\O), Drain-Source On-Resistance V<sub>cs</sub> 10V 9V 8V 7V 6V 5V 4.5V 90 80 70 60 50 40 30 20 10 0 0 20 40 I<sub>D</sub>, Drain Current (A)

**Figure 5: On-Region Characteristics** 

Figure 6: Typ. RDS Variation vs. I<sub>D</sub> and V<sub>GS</sub>



N 2 2 25 Q<sub>G</sub>, Total Gate Charge (nC)

Figure 7: Typ. Capacitance Characteristics

Figure 8: Typ. Gate Charge Characteristics



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#### **Ratings and Characteristics Curves**

# (T<sub>A</sub> = 25°C unless otherwise specified)

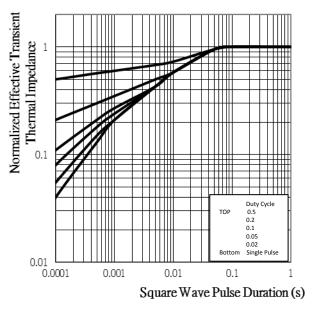


Figure 9: Normalized Thermal Transient Impedance, Junction-to-Case

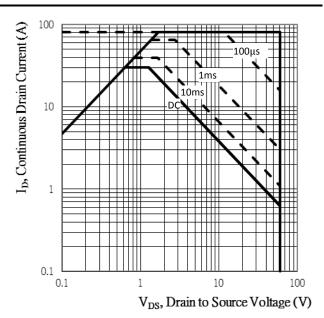


Figure 10: Maximum Safe Operation Area



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# 3. Marking information

**Top Marking Rule** 

PFC PRM
021N06N5
YYWW ABSH

PRM021N06N5 = Product Type Marking Code

YYWW = Date Code

YY = Last two digits of year

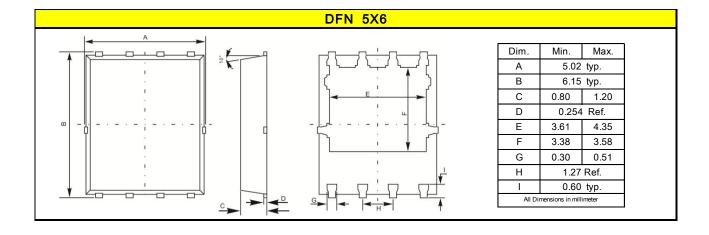
WW = Week code

ABS = Assembly code

H = Halogen Free (N/A = common molding compound)

## 4. Package information

Package Outline Dimensions millimeters





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### 5. Ordering information

Part Number	Package	Delivery mode
PRM021N06N5	DFN 5X6	3000 pcs / 13" diameter reel

#### Mechanical

Molder Plastic: UL Flammability Classification Rating 94V-0
 Device Weight: 0.003 ounces (0.093grams) – DFN 5X6

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